

Amendment

Amendment to the Claims

1. (currently amended) A MOS array having a single at least one polygate supporting a plurality of sources that are electrically connected to each other and provided with a source contact and a plurality of drains that are electrically connected to each other and provided with a drain contact, each source being located opposite a drain in parallel, wherein the polygate has a non-uniform length along its width, with decreasing length as the distance from the drain contact increases.
2. (original) A MOS array of claim 1, wherein the array includes a common drain interconnect and a common source interconnect.
3. (currently amended) A MOS array of claim 2, wherein the drains and sources interconnects have define a comb-like configuration.
4. (currently amended) A MOS array of claim 3, wherein, the drains and sources interconnects are opposed and staggered to define alternating drain and source regions on ~~either side~~ both sides of the polygate and extending substantially along the width of the polygate.
5. (original) A MOS array of claim 2, wherein the drain interconnect and source interconnect each have at least one metal contact with the length of the polygate being shorter at greater distances from the at least one contact.
6. (currently amended) A MOS array of claim 5, wherein the array has only one drain contact and one source contact when ~~if~~ the drains and sources regions do not alternate.
7. (currently amended) A MOS array of claim 5, wherein the array has a drain contact on each side of the polygate and a source contact on each side of the polygate to support ~~staggered~~ alternating drain and source regions on each side of the polygate.

8. (original) A MOS array of claim 5, wherein each drain contact is located in the middle of a drain interconnect and each source contact is located in the middle of a source interconnect.
9. (original) A MOS array of claim 8, wherein the polygate is longer in the middle and gets shorter towards the ends.
10. (original) A MOS array of claim 1, wherein the change in length of the polygate is non-linear.
11. (original) A MOS array of claim 9, wherein the change in length of the polygate is non-linear.
12. (original) A MOS array of claim 10, wherein the decrease in length of the polygate further away from the drain and source contacts corresponds to the increase in resistance along the interconnect as one moves further from the drain and source contacts.
13. (original) A MOS array of claim 11, wherein the decrease in length of the polygate further away from the drain and source contacts corresponds to the increase in resistance along the interconnect as one moves further from the drain and source contacts.